

DERWENT-ACC-NO: 2002-023389  
DERWENT-WEEK: 200203  
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TITLE: Dry etching of oxide film involves using  
fluorocarbon gas containing  
sulfur

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PRIORITY-DATA: 1999KR-0029535 (July 21, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES	MAIN-IPC	
KR 2001010568	February 15, 2001	N/A
001	C23C 016/00	
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APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
KR2001010568A	N/A	1999KR-0029535
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INT-CL (IPC): C23C016/00

ABSTRACTED-PUB-NO: KR2001010568A

BASIC-ABSTRACT: NOVELTY - Provided is a method of dry  
etching of an oxide film,  
which increases etching selection ratio to a nitride film  
by side product  
non-volatile and unstable and prevents global warming  
because decomposition is  
easy in the atmosphere by using fluorocarbon gas containing  
sulfur as an  
etching gas.

DETAILED DESCRIPTION - The method of dry etching of the  
oxide film using the  
nitride film as etching a barrier layer is characterized by  
providing the

etching gas composed of fluorocarbon gas containing sulfur  
that is C4F8S,  
C3F6S, C3F6S2, hydrofluorocarbon (HFC) containing sulfur or  
mixture thereof, and  
the etching gas can contain further oxygen, gas contained  
oxygen, a  $C_xF_y$  (  $x =$   
1-6 and  $y = 2-12$ ) gas, a  $C_xH_yF_z$  (  $x = 1-6$ ,  $y = 1-4$  and  $z =$   
2-10) gas, an inert  
gas or mixture thereof.

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CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS:

DRY ETCH OXIDE FILM FLUOROCARBON GAS CONTAIN

DERWENT-CLASS: E16 L03

CPI-CODES: E10-F01; E10-H04A3; E31-F04; L04-C07B;

SECONDARY-ACC-NO:

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